

Silicon NPN Epitaxial

2SC4366

■ Features

- Low Frequency amplifier.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	60	V
Collector-emitter voltage	V_{CE0}	50	V
Emitter-base voltage	V_{EB0}	15	V
Collector current	I_C	300	mA
Collector dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C = 10\mu\text{A}$, $I_E = 0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}$	$I_C = 1\text{mA}$, $R_{BE} = \infty$	50			V
Emitter-base breakdown voltage	$V_{(BR)EB0}$	$I_E = 10\mu\text{A}$, $I_C = 0$	15			V
Collector cutoff current	I_{CBO}	$V_{CB} = 50\text{V}$, $I_E = 0$			1	μA
Base-emitter voltage	V_{BE}	$V_{CE} = 6\text{V}$, $I_C = 1\text{mA}$			0.75	V
DC current gain	h_{FE}	$V_{CE} = 6\text{V}$, $I_C = 100\text{mA}$	800		2000	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 300\text{mA}$, $I_B = 30\text{mA}$			0.3	V

■ Marking

Marking	ZI-